

Amendments to the Claims

This listing will replace all prior versions, and listing, of claims in the application.

Claims 1-24. (cancelled)

25. (currently amended) A multilevel interconnect structure, comprising:

a semiconductor surface that has been provided with metal points of electrical contact in said surface, there-  
over having been created a low k compound layer of inter  
metal dielectric comprising:

(1) a first layer of dielectric deposited on said  
semiconductor surface, said first layer of dielectric  
containing comprising a first network of trenches filled  
with air;

(2) a second layer of dielectric deposited on and in  
contact with said first layer of dielectric on said  
semiconductor surface, said second layer of dielectric  
containing comprising a second network of trenches filled  
with air, whereby said second network of trenches is being  
in physical contact with and intersects intersecting with

said first network of trenches to form an interconnected network of trenches filled with air~~under an angle~~; and

(3) a layer of oxide deposited over said second layer of dielectric, said layer of oxide comprising:

(i) a first layer of oxide having openings created there-through, said openings being aligned with the intersections between said first and second network of trenches, enabling creation of said first and second network of trenches; and

(ii) a second layer of oxide, said second layer of oxide closing the openings in the first layer of oxide.

26. (currently amended) The multilevel interconnect structure of claim 25, ~~whereby furthermore~~ additionally a network of metal interconnects ~~interconnect lines is created on having been created over said three layers of dielectric said layer of oxide.~~

27. (currently amended) The multilevel interconnect structure of claim 25, ~~whereby furthermore~~ said layer of oxide deposited over said second layer of dielectric ~~trenches is extended in~~ having a thickness between about 1000 and 4000 Angstroms.

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28. (currently amended) The multilevel interconnect structure of claim 27 whereby furthermore a network of metal interconnect lines is created on said layer of oxide deposited over said second layer of dielectric ~~extended layer of oxide.~~